

Form 1449*	Atty. Docket No.: 303.354US2	Serial No. Unknown
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Leonard Forbes et al.	09/135,413
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Viet Q. Nguyen
Primary Examiner

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Examiner V. Nguyen	Date Considered 5/18/00
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Sheet 1 of 1

Form 1449*	Atty. Docket No.: 303.354US2	Serial No. 09/135,413
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Leonard Forbes et al.	
	Filing Date: August 14, 1998	Group: 2818

U.S. PATENT DOCUMENTS

**Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
<i>VQ</i>	4,460,670	07/01/1984	Ogawa, et al.	430	57	
<i>VQ</i>	4,657,699	04/01/1987	Nair	252	51	
<i>VQ</i>	4,688,725	04/01/1998	Yoshida, et al.	136	258	
<i>VQ</i>	4,688,725	09/06/1988	Horiuchi, M., et al.	357	23.8	06/19/87
<i>VQ</i>	5,145,741	09/01/1992	Quick	428	402	
<i>VQ</i>	5,604,357	02/18/1997	Hori, T.	257	24	07/11/95
<i>VQ</i>	5,629,222	05/13/1997	Yamazaki, S., et al.	438	259	04/28/95
<i>VQ</i>	5,740,104	04/14/1998	Forbes, L.	365	185.03	01/29/97
<i>VQ</i>	5,801,401	09/01/1998	Forbes, L.	257	77	

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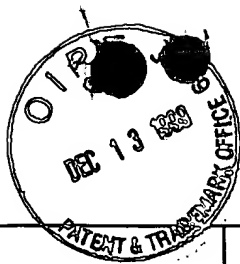
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Examiner <i>V. Nguyen</i>	Date Considered <i>5/19/00</i>
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VN	5,049,950	09/17/1991	Fujii, Y., et al.	357	2	08/09/90
VN	5,371,383	12/06/1994	Miyata, K., et al.	257	77	05/14/93
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VN	Sakata, I., et al., "Amorphous Silicon/Amorphous Silicon Carbide Heterojunctions Applied to Memory Device Structures", <u>Electronics Letters</u> , 30(9), pp. 688-689, (April 28, 1994)
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Examiner

V. NGUYEN

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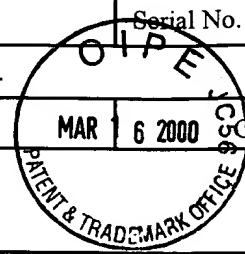
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**Examiner		Document Number	Date	Name	Class	Subclass	Filing Date
Initial							If Appropriate
VN		5,235,195	08/10/1993	Tran, N.T., et al.	257	59	10/19/92
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Initial							Yes	No

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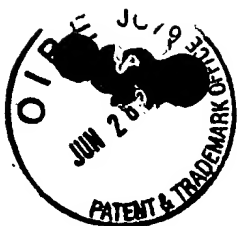
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**Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
VN	5,886,368	03/23/1999	Forbes, L., et al.	257	77	07/29/97
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VN	Sze, S.M., In: Physics of Semiconductor Devices, Wiley-Interscience, New York, p. 496-497, (1969)

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